

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	20	noda-takaaki.in.	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 14:42
L2	7	suzaki-kenichi.in.	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 14:42
L3	4060	(427/248.1,255.23,255.28,255.38,255.395).CCLS.	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	OFF	2008/02/12 14:48
L4	2987	(438/478,758,800,900,909,932,935).CCLS.	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	OFF	2008/02/12 14:52
L5	5	(L1 L2) and purge and (silicon monosilane) and (boron)	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 14:55
L6	160	(L3 L4) and purge and (silicon monosilane) and (boron)	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 14:55
L7	2	("6171104").PN.	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	OFF	2008/02/12 14:57

L8	8	((L3 L4) and ((purge with (inert adj gas)) same (chamber furnace reactor)) and (silicon monosilane) and ((doped doping) with boron)	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 15:03
L9	97	((purge with (inert adj gas)) same (chamber furnace reactor)) and (silicon monosilane) and ((doped doping) with boron)	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 15:03
L10	289	((purge with (inert adj gas)) same (chamber furnace reactor)) and (silicon monosilane) and (boron)	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 15:06
L11	235	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) same (silane silicon) same (boron "bcl.sub.3")	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 15:59
L12	12	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) same (silane silicon) same (boron "bcl.sub.3") same purg\$3	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:00
L13	0	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) same (silane silicon) same (boron "bcl.sub.3") and (purg\$3 with clean\$3 with (chamber reactor furnace))	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:14
L14	8	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) same (silane silicon) same (boron "bcl.sub.3") and (purg\$3 with (clean\$3 evacuat\$3) with (chamber reactor furnace))	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:15
L15	21	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) same (silane silicon) same (boron "bcl.sub.3") and (purg\$3 with (clean\$3 evacuat\$3))	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:16
L16	3	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) same (silane silicon) same (boron "bcl.sub.3") and (purg\$3 with (clean\$3))	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:16

L17	18	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) same (silane silicon) same (boron "bcl.sub.3") and (purg\$3 with remov\$3 with (substrate wafer))	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:19
L18	0	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) same (silane silicon) same (boron "bcl.sub.3") and (purg\$3 with (remov\$3 near2 (substrate wafer)))	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:20
L19	67	(silane silicon) same (boron "bcl.sub.3") and (purg\$3 with (remov\$3 near2 (substrate wafer)))	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:20
L20	47	(silane silicon) same (boron "bcl.sub.3") and (purg\$3 with (remov\$3 near1 (substrate wafer)))	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:23
L21	7	("20030053893" "20030077150" "5540098" "6066210" "6143083" "6573178").PN. OR ("6720274").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/12 16:29
L22	3	("20030180556" "6323139" "6468903").PN. OR ("6790793").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/12 16:29
L23	3	("5637153" "5963834").PN. OR ("6573178").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/12 16:32
L24	2	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) same (silane monosilane) same ((boron adj trichloride) "bcl.sub.3")	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:44
L25	7	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) same (silane silicon "sih. sub.4" monosilane) same ((boron adj trichloride) "bcl.sub.3")	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:46
L26	25	(ald (atomic adj layer adj deposit\$3) (cyclic adj deposit\$3) (atomic adj layer adj epitaxy)) and ((silane monosilane) same ((boron adj trichloride) "bcl.sub.3"))	US-PGPUB; USPAT; DERWENT; IBM_TDB	OR	ON	2008/02/12 16:50

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